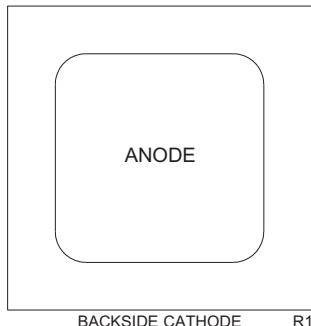


CPD24-CMR1F-06M

Fast Rectifier Die

1.0 Amp, 600 Volt

The CPD24-CMR1F-06M is a silicon 1.0 Amp, 600 Volt fast recovery rectifier ideal for all types of commercial, industrial, entertainment, and computer applications.



MECHANICAL SPECIFICATIONS:

Die Size	51 x 51 MILS
Die Thickness	11 MILS
Anode Bonding Pad Size	35 x 35 MILS
Top Side Metalization	Ni/Au – 5,000Å/2,000Å
Back Side Metalization	Ni/Au – 5,000Å/2,000Å
Scribe Alley Width	2.0 MILS
Wafer Diameter	4 INCHES
Gross Die Per Wafer	4,250

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

	SYMBOL		UNITS
Peak Repetitive Reverse Voltage	V_{RRM}	600	V
DC Blocking Voltage	V_R	600	V
RMS Reverse Voltage	$V_{R(\text{RMS})}$	420	V
Average Forward Current	I_O	1.0	A
Peak Forward Surge Current, $t_p=8.3\text{ms}$	I_{FSM}	30	A
Operating and Storage Junction Temperature	T_J, T_{stg}	-65 to +150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS: ($T_A=25^\circ\text{C}$ unless otherwise)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_R	$V_R=600\text{V}$		5.0	μA
I_R	$V_R=600\text{V}, T_A=125^\circ\text{C}$		200	μA
V_F	$I_F=1.0\text{A}$		1.3	V
t_{rr}	$I_F=0.5\text{A}, I_R=1.0\text{A}, I_{rr}=0.25\text{A}$		250	ns

PACKING OPTIONS:

- CPD24-CMR1F-06M-CT: Singulated die in waffle pack; 400 die per tray.
- CPD24-CMR1F-06M-WN: Full wafer, unsawn, 100% tested with reject die inked.
- CPD24-CMR1F-06M-WR: Full wafer, sawn and mounted on plastic ring, 100% tested with reject die inked.

CPD24-CMR1F-06M

Typical Electrical Characteristics

Central
semiconductor Corp.
www.centralsemi.com

